## INFORMATION DISCLOSURE CITATION

at sheets if necessary)

ATTY, DOCKET NO.

1035-548

10/516.333

APPLICANT

Morito AKIYAMA et al.

FILING DATE

TC/A.U.

November 30, 2004

unassigned

**U.S. PATENT DOCUMENTS FILING DATE 'EXAMINER** <u>CLASS</u> SUBCLASS IF APPROPRIATE DOCUMENT NUMBER INITIAL DATE NAME **FOREIGN PATENT DOCUMENTS** TRANSLATION CLASS SUBCLASS DOCUMENT DATE COUNTRY YES NO JP 2002-344279 (A) 11/2002 Japan ABSTRACT JP 2003-198319 (A) 07/2003 Japan ABSTRACT OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.) Low-temperature growth of piezoelectric AIN film by rf reactive planar magnetron sputtering", T. Shiosaki et al., Appl. Phys. Lett. 36(8), 15 April 1980, 643-645, © 1980 American Institute of Physics Structural and electroacoustic studies of AIN thin films during low temperature radio frequency sputter deposition", F. Engelmark et al., J. Vac. Sci. Technol. A19(5), Sep/Oct 2001, 2664-2669, © 2001 American Vacuum Society Structural properties of AIN films grown on Si, Ru/Si and ZnO/Si substrates", Won Taeg Lim et al., Thin solid Films 382(2001) 56-60, @ 2001 Elsevier Science Synthesis and Surface Acoustic Wave Property of Aluminum Nitride Thin films Fabricated on Silicon and Diamond Substrates Using the Sputtering Method", M. Ishihara et al., Jpn. J. Appl. Phys, vol. 40(2001) pp. 5065-5068 Part 1, No. 8, August, © 2001 The Japan Society of Applied Physics 'Deposition of AIN thin film using reactive sputtering method", Y. Honda et al., Reports of Kumamoto Industrial ۲P Research Institute No. 35, 1997, pp. 59-63 @ Kumamoto Industrial Research Institute \*Examiner **Date Considered** 

Examiner; Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Sheet 1 of 1		IDS #0405					
INFORMATION DISCLOSURE · CITATION		ATTY.	DOCKET NO.	SERIAL NO.			
		035-548		1 6,333			
		APPLIC	CANT				
		Mori	to AKIYAMA et al.				
(Use several sheets if necessary)		FILING DATE		TC/A.U.			
		November 30, 2004		unassigned			
		T					
*EXAMINER		U	J.S. PATENT DOCUMENTS			FILING	DATE
INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	IF APPR	OPRIATE
		<u> </u>			<del>                                     </del>		
					-		
						<u> </u>	
		FOF	REIGN PATENT DOCUMENTS			TRANS	LATION
	DOCUMENT	DATE	COUNTRY	. CLASS	SUBCLASS	YES	NO
EP	1 124 269 A2	08/16/2001	EP		_		
<u>Sp</u>	GB 0426814.0 (Exam Report)	3/10/2005	GB	-	_		
		<u> </u>					
-	_						
	OTHER DOCI	JMENIS (ir	ncluding Author, Title, Date, Pert	inent pages, et	ic.)		
				<del></del>			
	1 5	b 1	_	1 ~ /-	7/22		

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Oraw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

\*Examiner

Date Considered